

LIGHT EMITTING DIOEE STRUCTURE AND MANUFACTURE METHOD THEREOF

ABSTRACT OF THE DISCLOSURE

A light emitting diode (LED) structure and manufacture method thereof are disclosed, wherein a buffer layer is grown on a substrate and then an LED structural layer is grown on the buffer layer. The LED structural layer comprises a p-type quantum-dot epitaxial layer on a p-type GaN layer. As the p-type quantum-dot epitaxial layer has a coarsening and scattering effect, the path of light emitted from an INGaN multiple-quantum-well structural layer is changed. Therefore, it is possible to lessen the probability of total reflection and thereby heighten the light-emitting efficiency of LED.